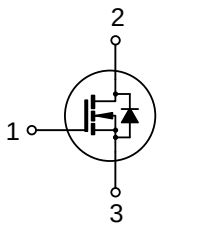
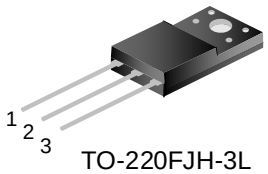
11A, 650V SUPER JUNCTION MOS POWER TRANSISTOR

DESCRIPTION

SVSP11N65FJHD2 is an N-channel enhancement mode high voltage power MOSFETs produced using Silan's super junction MOS technology. It achieves low conduction loss and switching losses. It leads the design engineers to their power converters with high efficiency, high power density, and superior thermal behavior. Furthermore, it's universal applicable, i.e., suitable for hard and soft switching topologies.



1.Gate 2.Drain 3.Source



TO-220FJH-3L

FEATURES

- 11A, 650V, $R_{DS(on)(typ.)}$=0.33Ω@V_{GS}=10V
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- High peak current capability

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVSP11N65FJHD2	TO-220FJH-3L	P11N65FJH	Halogen free	Tube

ABSOLUTE MAXIMUM RATINGS (UNLESS OTHERWISE NOTED, T_J=25°C)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	±30	V
Drain Current	T_C=25°C	I_D	11	A
	T_C=100°C		7	
Drain Current Pulsed		I_{DM}	44	A
Power Dissipation (T_C=25°C)		P_D	35	W
-Derate above 25°C			0.28	W/°C
Single Pulsed Avalanche Energy (Note1)		E_{AS}	250	mJ
Reverse Diode dv/dt	(Note 2)	dv/dt	15	V/ns
MOSFET dv/dt Ruggedness	(Note 3)	dv/dt	50	V/ns
Operation Junction Temperature Range		T_J	-55～+150	°C
Storage Temperature Range		T_{stg}	-55～+150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.57	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

ELECTRICAL CHARACTERISTICS (UNLESS OTHERWISE NOTED, T_C=25°C)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	650	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V	--	--	1.0	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	2.0	--	4.0	V
Static Drain- Source on State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=5.5A	--	0.33	0.4	Ω
Gate Resistance	R_g	f=1MHz	--	5.2	--	Ω
Input Capacitance	C_{iss}	f=1MHz,V_{GS}=0V, V_{DS}=100V	--	632	--	pF
Output Capacitance	C_{oss}		--	37	--	
Reverse Transfer Capacitance	C_{rss}		--	2.3	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=325V, V_{GS}=10V, R_G=24Ω, I_D=11A (Notes 4, 5)	--	12	--	ns
Turn-on Rise Time	t_r		--	35	--	
Turn-off Delay Time	$t_{d(off)}$		--	64	--	
Turn-off Fall Time	t_f		--	31	--	
Total Gate Charge	Q_g	V_{DD}=520V, V_{GS}=10V, I_D=11A (Notes 4,5)	--	23	--	nC
Gate-Source Charge	Q_{gs}		--	5.3	--	
Gate-Drain Charge	Q_{gd}		--	11	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	11	A
Pulsed Source Current	I_{SM}		--	--	44	
Diode Forward Voltage	V_{SD}	I_S=11A, V_{GS}=0V	--	--	1.4	V
Reverse Recovery Time	T_{rr}	I_S=11A, V_{GS}=0V, dI_F/dt=100A/μs (Note 4)	--	361	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.9	--	μC

Notes:

1. L=79mH, I_{AS}=2.4A, V_{DD}=100V, R_G=25Ω, starting temperature T_J=25°C;
2. V_{DS}=0~400V, I_{SD}<=11A, T_J=25°C;
3. V_{DS}=0~480V;
4. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%;
5. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

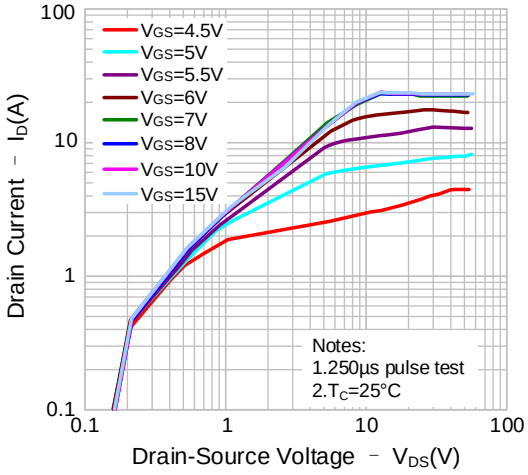


Figure 2. Transfer Characteristics

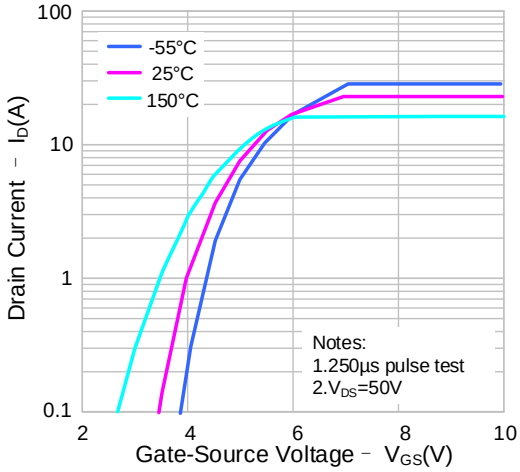


Figure 3. On-Resistance Variation vs. Drain Current

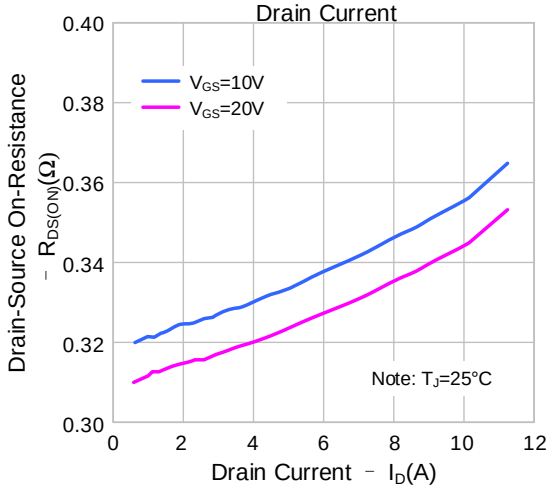


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

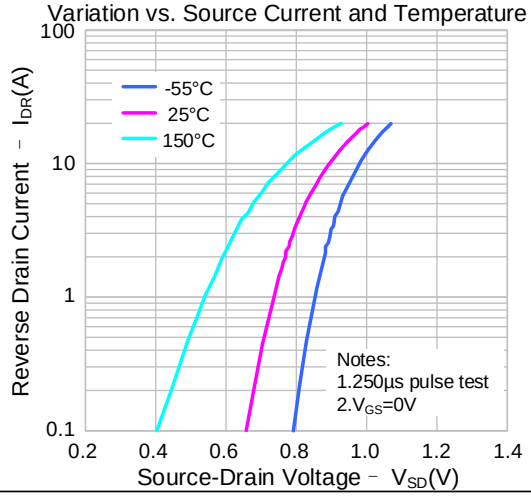


Figure 5. Capacitance Characteristics

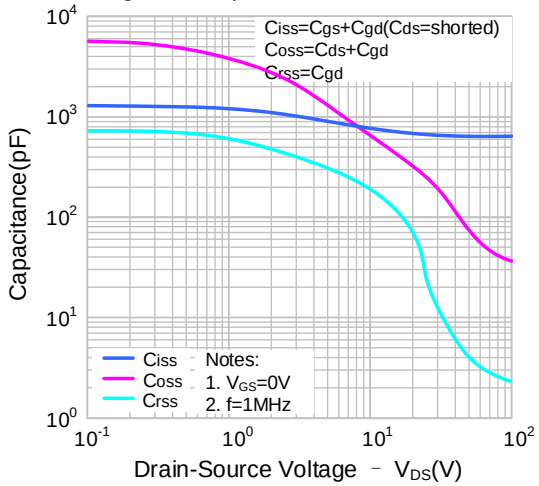
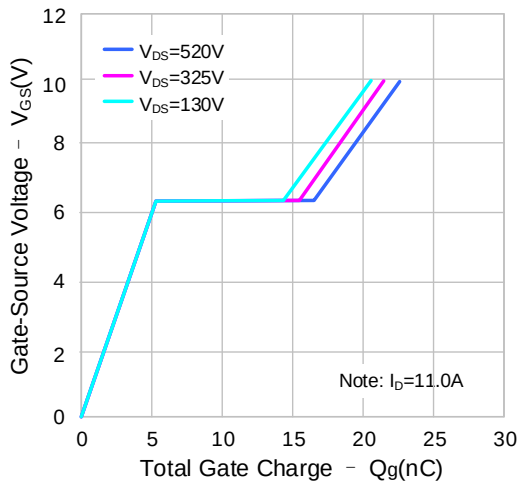


Figure 6. Gate Charge Characteristics



TYPICAL CHARACTERISTICS (CONTINUED)

Figure 7. Breakdown Voltage Variation vs. Temperature

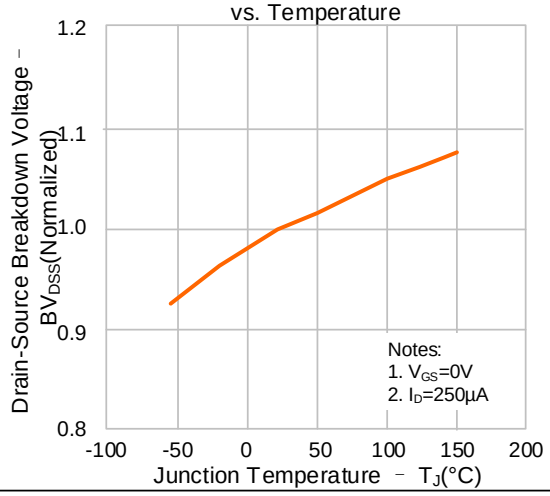


Figure 8. On-resistance Variation vs. Temperature

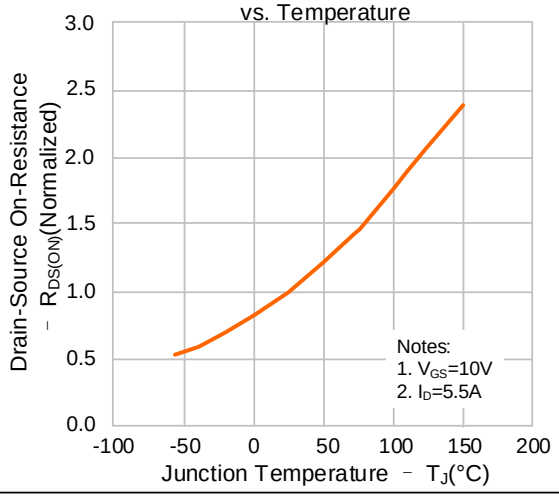
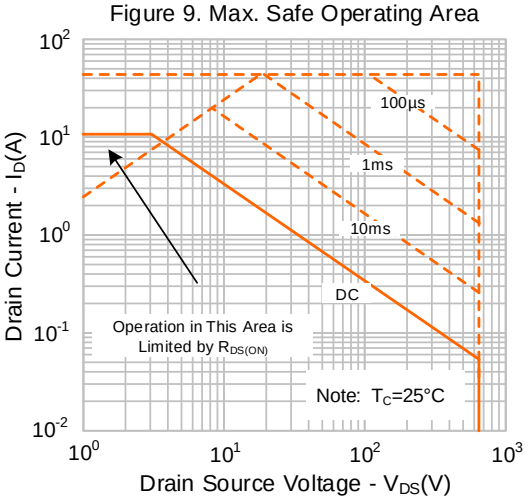
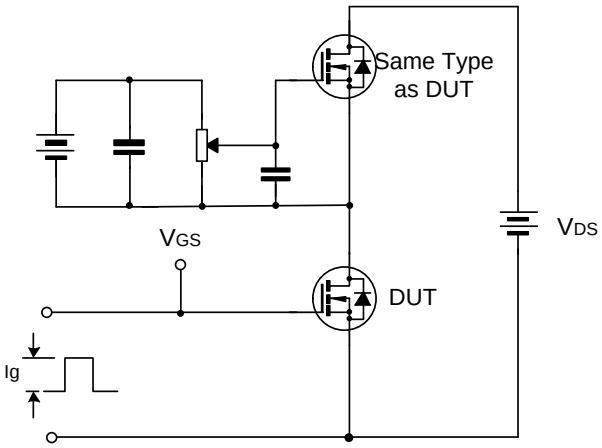


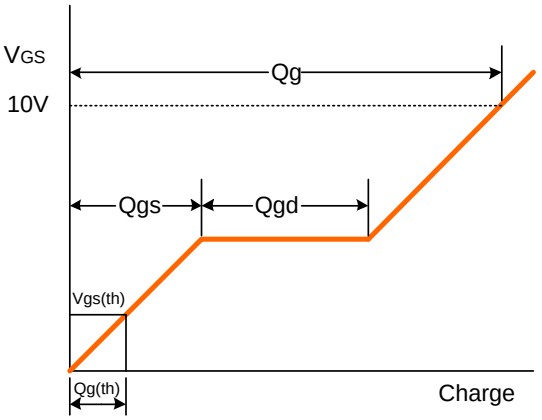
Figure 9. Max. Safe Operating Area



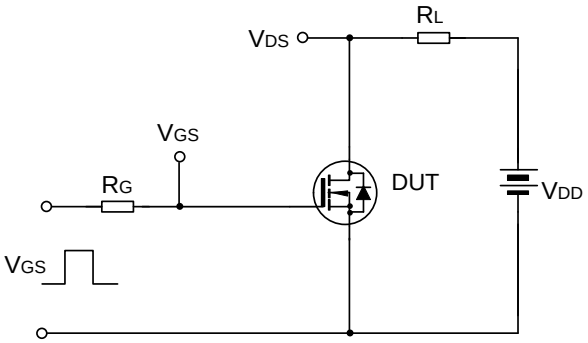
TYPICAL TEST CIRCUIT

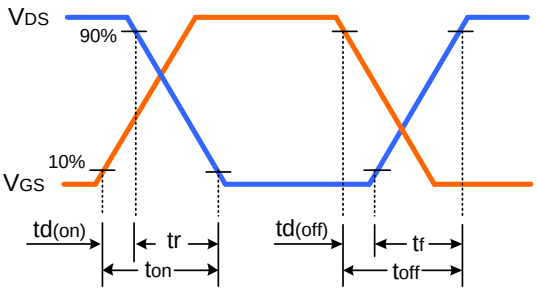
Gate Charge Test Circuit & Waveform



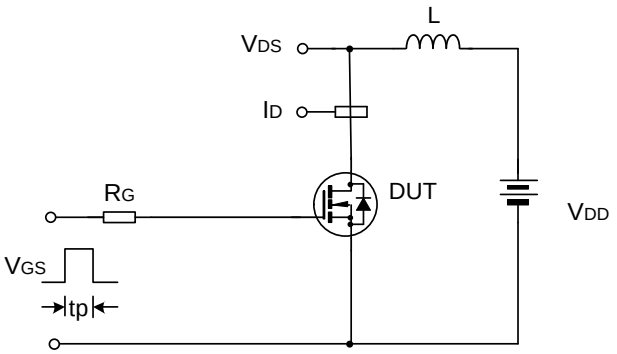


Resistive Switching Test Circuit & Waveform

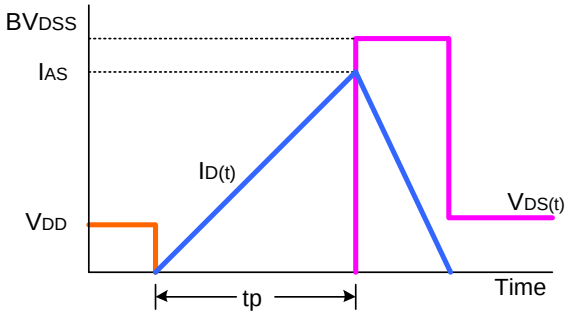




Unclamped Inductive Switching Test Circuit & Waveform

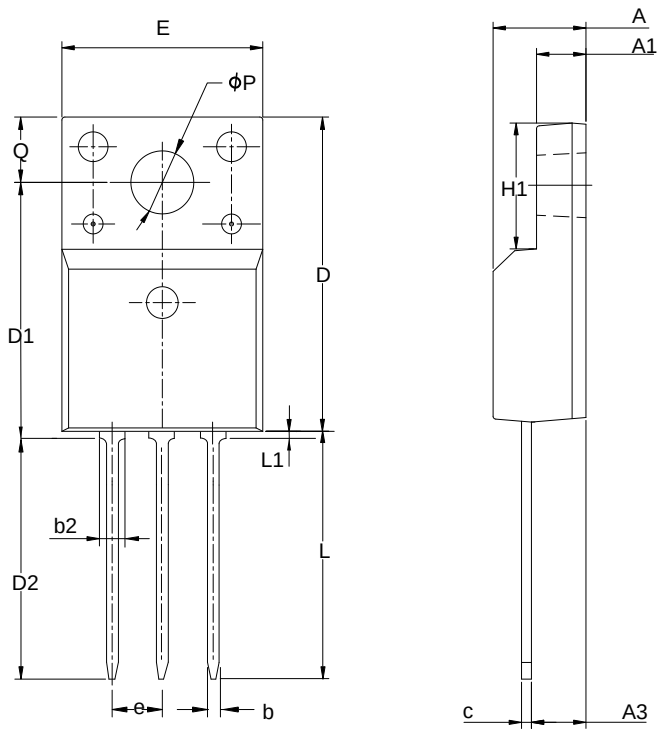


$$E_{AS} = \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



PACKAGE OUTLINE

TO-220FJH-3L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.55	0.70	0.80
b2	—	—	1.29
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	12.87	13.07	13.27
D2	12.28	12.48	12.68
E	9.73	10.16	10.36
e	2.54BCS		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	—	—	0.85
ϕP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Important notice :

1. **The instructions are subject to change without notice!**
2. **Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current. Please read the instructions carefully before using our products, including the circuit operation precautions.**
3. **Our products are consumer electronic products or the other civil electronic products.**
4. **When using our products, please do not exceed the maximum rating of the products, otherwise the reliability of the whole machine will be affected. There is a certain possibility of failure or malfunction of any semiconductor product under specific conditions. The buyer is responsible for complying with safety standards and taking safety measures when using our products for system design, sample and whole machine manufacturing, so as to avoid potential failure risk that may cause personal injury or property loss.**
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Rev.: 1.0

Revision History:

1. First release